

60 V, 600 mA, PNP switching transistor 10 October 2014

Product data sheet

1. General description

PNP switching transistor in a medium power flat lead SOT89 (SC-62/TO-243) Surface-Mounted Device (SMD) plastic package.

NPN complement: PXT2222A

2. Features and benefits

- High current: max. 600 mA
- Low voltage: max. 60 V
- AEC-Q101 qualified

3. Applications

• Switching and linear amplification

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current			-	-	-600	mA
h _{FE}	DC current gain	V_{CE} = -1 V; I_C = -10 mA; T_{amb} = 25 °C		100	-	-	

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		в
3	В	base	3 2 1 SOT89	E sym132





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6. Ordering information

Table 3. Ordering inf	ormation					
Type number	Package					
	Name	Description	Version			
PXT2907A	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PXT2907A	1

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8. Limiting values

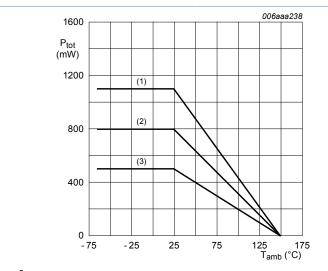
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-600	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-800	mA
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.5	W
			[2]	-	0.8	W
			<u>[3]</u>	-	1.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².



(1) FR4 PCB; 6 cm² mounting pad for collector.

- (2) FR4 PCB; 1 cm^2 mounting pad for collector.
- (3) FR4 PCB; standard footprint.

Fig. 1. Power derating curves

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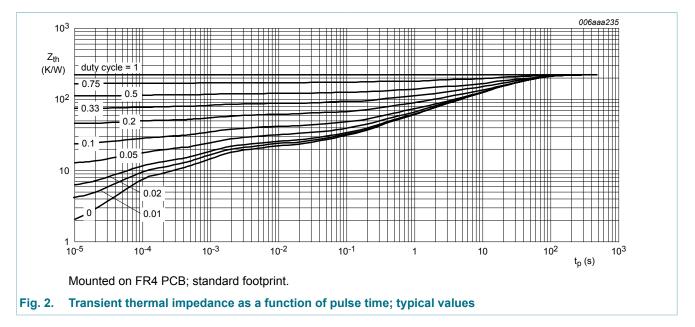
9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	156	K/W
			[3]	-	-	113	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

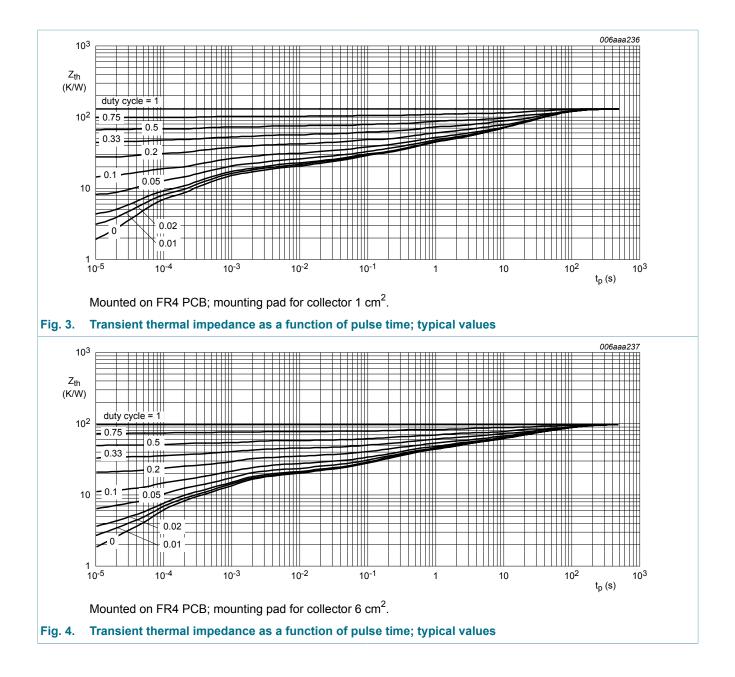
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².



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10. Characteristics

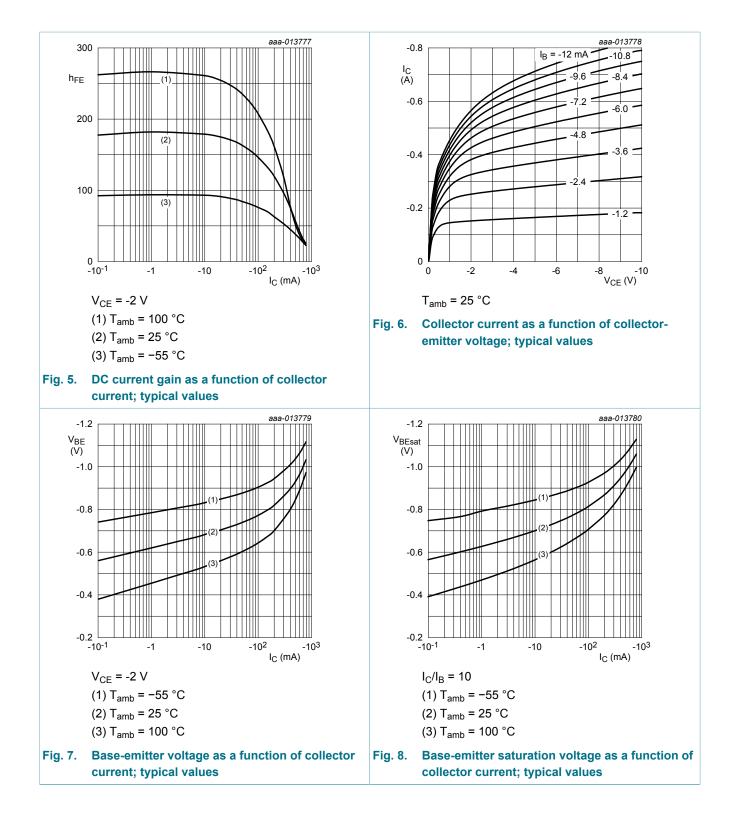
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-10	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _j = 125 °C	-	-	-10	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-50	nA
h _{FE}	DC current gain	V_{CE} = -1 V; I _C = -0.1 mA; T _{amb} = 25 °C	75	-	-	
		V_{CE} = -1 V; I _C = -1 mA; T _{amb} = 25 °C	100	-	-	
		V_{CE} = -1 V; I _C = -10 mA; T _{amb} = 25 °C	100	-	-	
		V_{CE} = -2 V; I _C = -150 mA; T _{amb} = 25 °C	100	-	300	
		V_{CE} = -10 V; I _C = -500 mA; T _{amb} = 25 °C	50	-	-	
02000	collector-emitter saturation voltage	I _C = -150 mA; I _B = -15 mA; T _{amb} = 25 °C	-	-	-400	mV
		I_{C} = -500 mA; I_{B} = -50 mA; T_{amb} = 25 °C	-	-	-1.6	V
V _{BEsat}	base-emitter saturation voltage	I _C = -150 mA; I _B = -15 mA; T _{amb} = 25 °C	-	-	-1.3	V
		I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-2.6	V
t _d	delay time	I _C = -150 mA; I _{Bon} = -15 mA;	-	-	12	ns
t _r	rise time	I _{Boff} = 15 mA; T _{amb} = 25 °C	-	-	30	ns
t _{on}	turn-on time	-	-	-	40	ns
t _s	storage time		-	-	300	ns
t _f	fall time	-	-	-	65	ns
t _{off}	turn-off time		-	-	365	ns
C _C	collector capacitance	V_{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	8	pF
C _E	emitter capacitance	V _{EB} = -500 mV; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	35	pF
f _T	transition frequency	V_{CE} = -20 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	200	-	-	MHz

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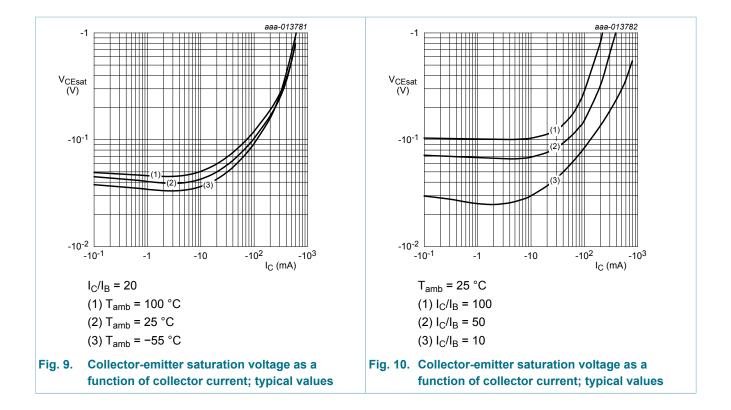
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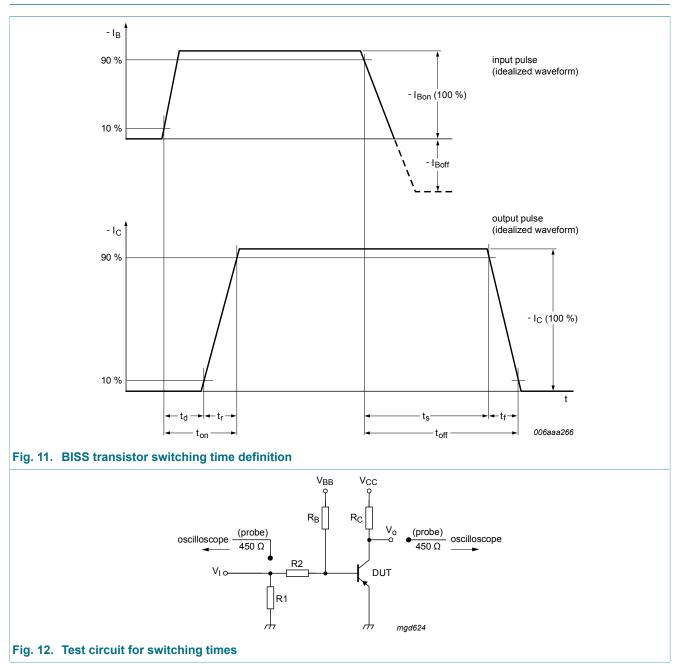
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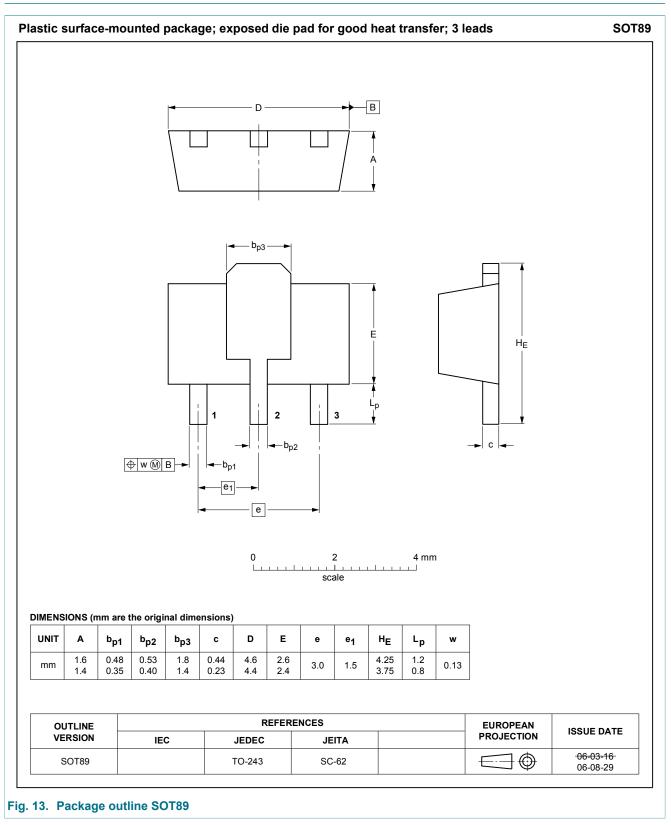
11. Test information



This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

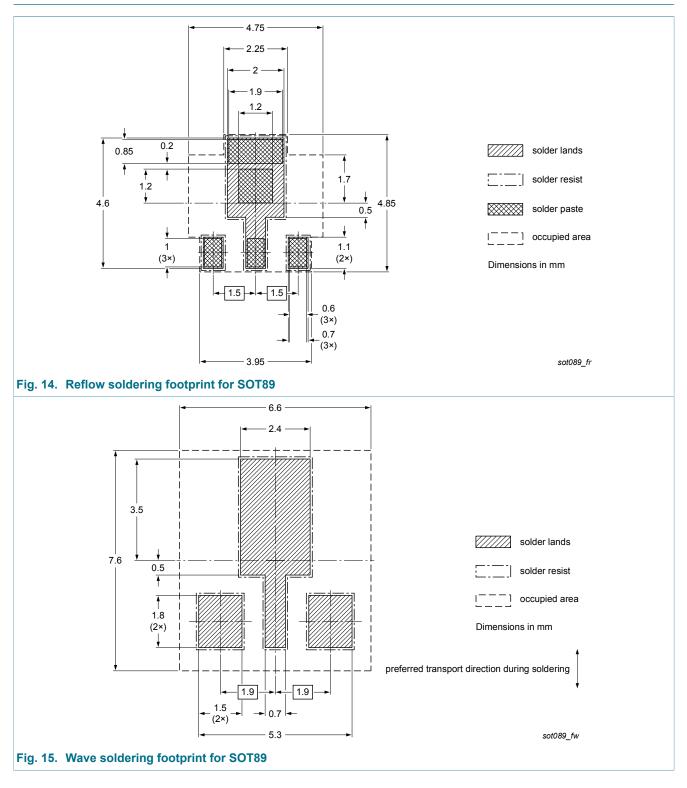


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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PXT2907A v.6	20141010	Product data sheet		PXT2907A v.5			
Modifications:	The format of this d of NXP Semicondu	ctors	signed to comply with the ompany name where app				
PXT2907A v.5	20041209	Product data sheet		PXT2907A v.4			
PXT2907A v.4	20020320	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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